JJMICROELECTRONICS

80V, 333A, 1.3mΩ N-channel Power SGT MOSFET

JMSH0802PTL

Features

- Excellent $R_{DS(ON)}$ and Low Gate Charge
- 100% UIS Tested
- 100% ΔVds Tested
- Halogen-free; RoHS-compliant

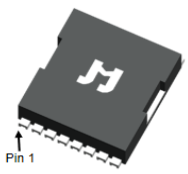
Applications

- Load Switch
- PWM Application
- Power Management

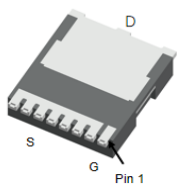
Product Summary

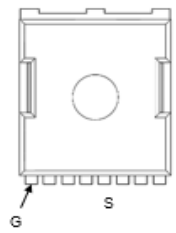
Parameters	Value	Unit
V_{DSS}	80	V
$V_{GS(th)\_Typ}$	2.9	V
I_D(@V_{GS}=10V)	333	A
$R_{DS(ON)\_Typ}$(@V_{GS}=10V	1.3	mΩ

RoHS

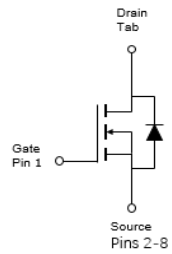


PowerJE®10x12





Pin Assignment



Schematic Diagram

Ordering Information

Device	Marking	MSL	Form	Package	Reel(pcs)	Per Carton (pcs)
JMSH0802PTL	SH0802P	1	Tape&Reel	PowerJE®10x12	2000	10000

Absolute Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DS}	Drain-to-Source Voltage		80	V
V_{GS}	Gate-to-Source Voltage		±20	V
I_D	Continuous Drain Current	T_C = 25°C	333	A
		T_C = 100°C	211	
I_{DM}	Pulsed Drain Current (1)		Refer to Fig.4	A
E_{AS}	Single Pulsed Avalanche Energy (2)		1765	mJ
P_D	Power Dissipation	T_C = 25°C	357	W
		T_C = 100°C	143	
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Max	Unit
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient(3)	35	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.35	

Electrical Characteristics (T_J = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D = 250μA, V_{GS} = 0V	80	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 64V, V_{GS} = 0V	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2.0	2.9	4.1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(4)	V_{GS} = 10V, I_D = 20A	-	1.3	1.8	mΩ
Dynamic Characteristics						
R_g	Gate Resistance	f = 1MHz	-	0.4	-	Ω
C_{iss}	Input Capacitance	V_{GS} = 0V, V_{DS} = 40V, f = 1MHz	9019	12627	17047	pF
C_{oss}	Output Capacitance		2423	3392	4579	pF
C_{rss}	Reverse Transfer Capacitance		55	77	103	pF
Q_g	Total Gate Charge	V_{GS} = 0 to 10V V_{DS} = 40V, I_D = 20A	136	190	257	nC
Q_{gs}	Gate Source Charge		43	60	81	nC
Q_{gd}	Gate Drain("Miller") Charge		29	40	54	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	V_{GS} = 10V, V_{DD} = 40V I_D= 20A, R_{GEN} = 3Ω	-	39	-	ns
t_r	Turn-On Rise Time		-	31	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	78	-	ns
t_f	Turn-Off Fall Time		-	33	-	ns
Body Diode Characteristics						
I_S	Maximum Continuous Body Diode Forward Current		-	-	333	A
I_{SM}	Maximum Pulsed Body Diode Forward Current		-	-	1333	A
V_{SD}	Body Diode Forward Voltage	V_{GS} = 0V, I_S = 20A	-		1.2	V
trr	Body Diode Reverse Recovery Time	I_F = 20A, di/dt = 100A/us	80	112	151	ns
Qrr	Body Diode Reverse Recovery Charge		-	318	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
2. E_{AS} condition: Starting T_J=25C, V_{DD}=40V, V_{GS}=10V, R_G=25ohm, L=3mH, I_{AS}=34.3A, V_{DD}=0V during time in avalanche.
3. $R_{\theta JA}$ is measured with the device mounted on a 1inch^2 pad of 2oz copper FR4 PCB.
4. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%.

Typical Performance Characteristics

Figure 1: Power De-rating

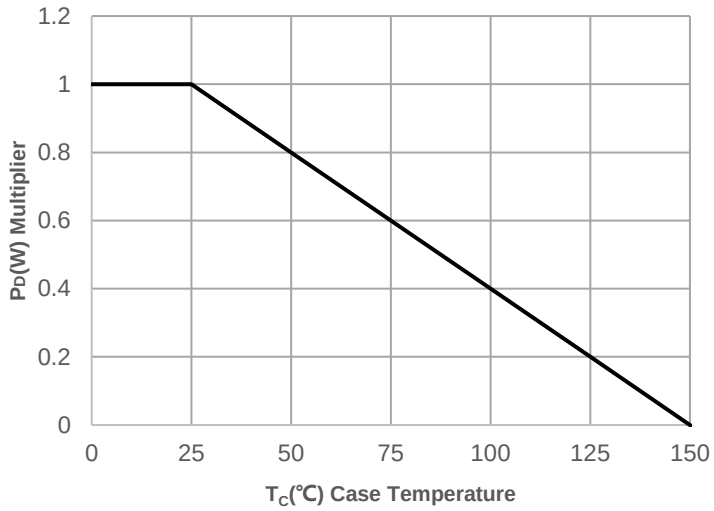


Figure 2: Current De-rating

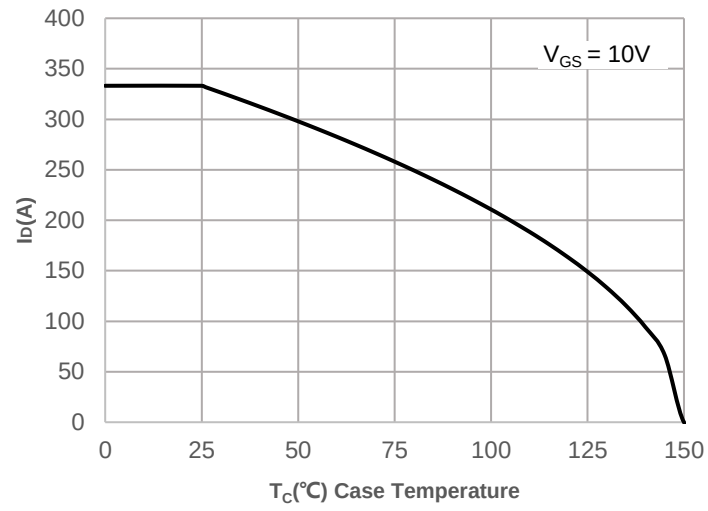


Figure 3: Normalized Maximum Transient Thermal Impedance

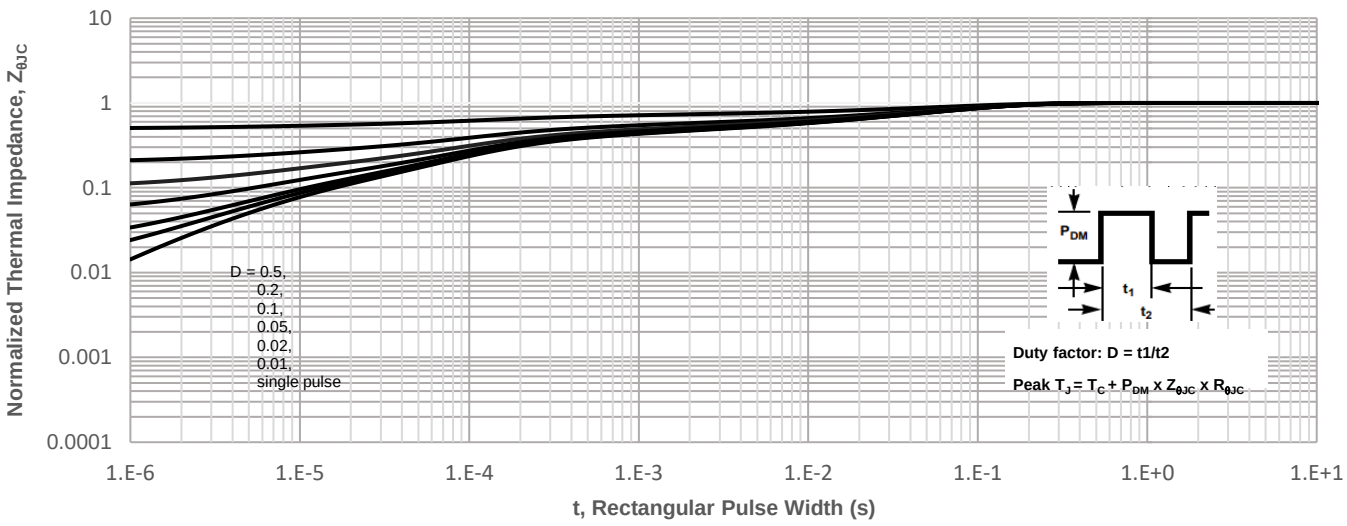
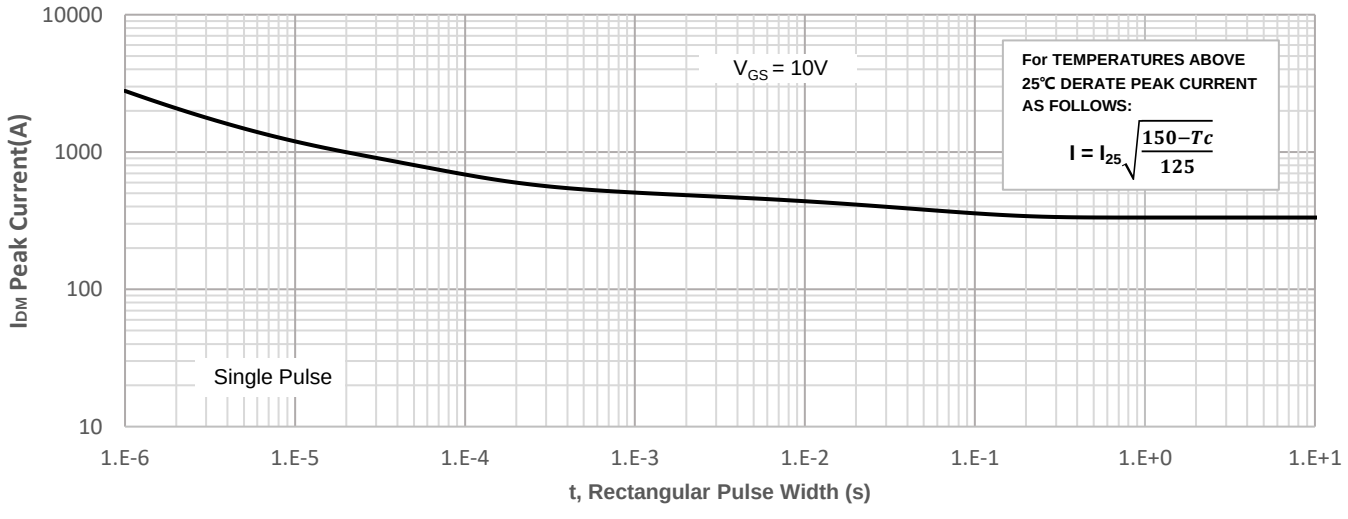


Figure 4: Peak Current Capacity



Typical Performance Characteristics

Figure 5: Output Characteristics

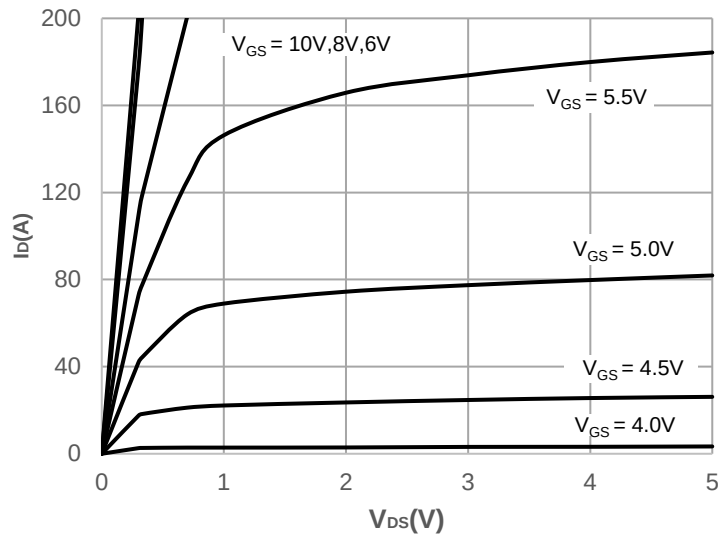


Figure 6: Typical Transfer Characteristics

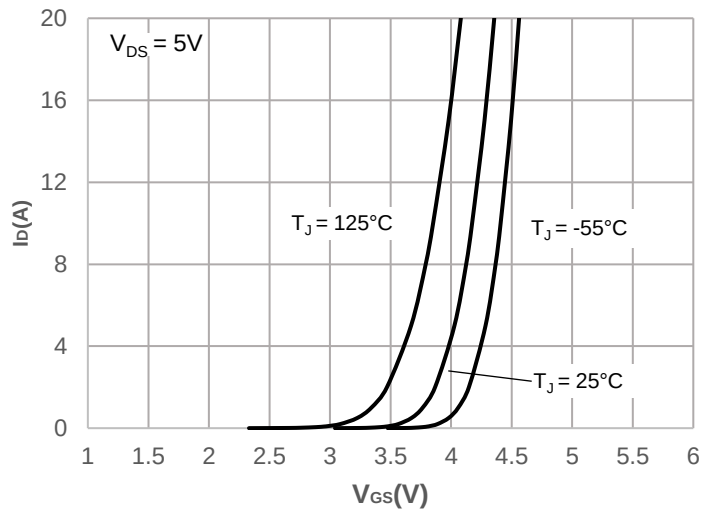


Figure 7: On-resistance vs. Drain Current

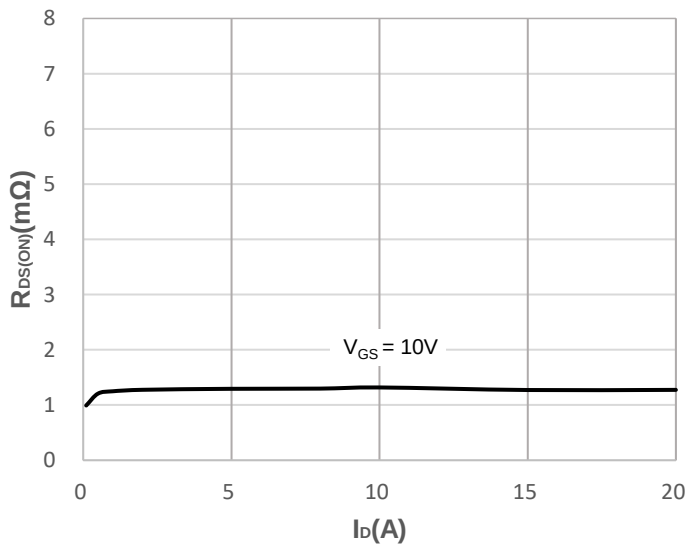


Figure 8: Body Diode Characteristics

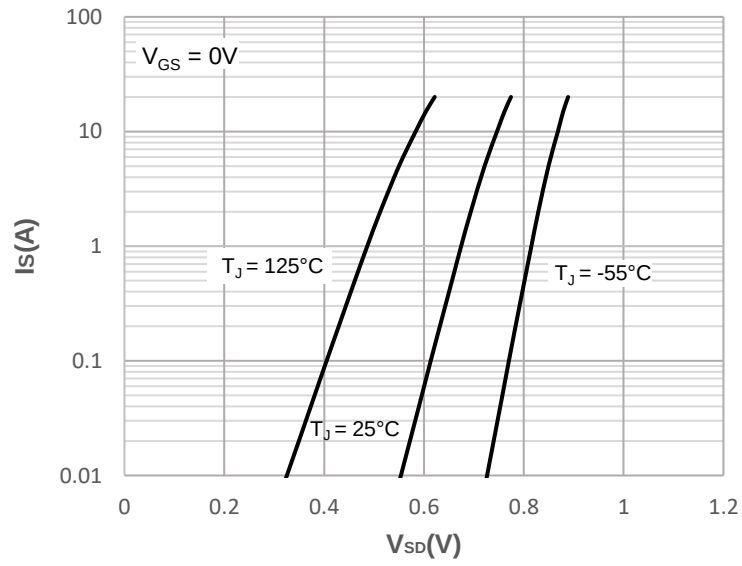


Figure 9: Gate Charge Characteristics

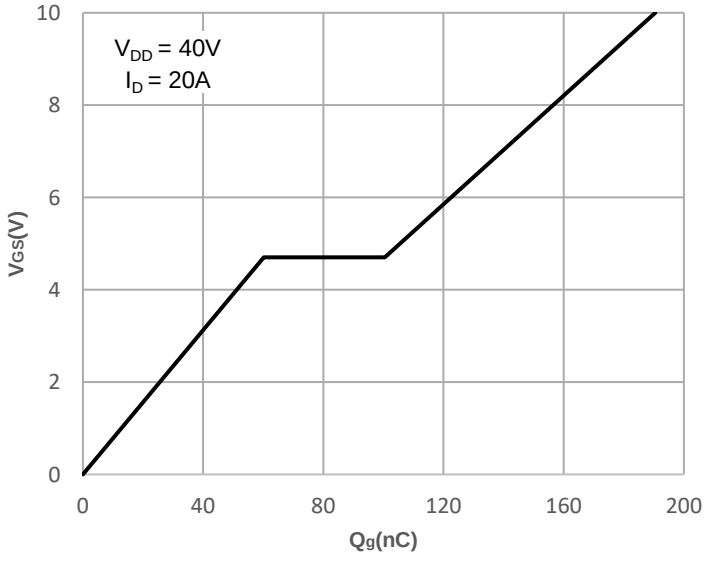
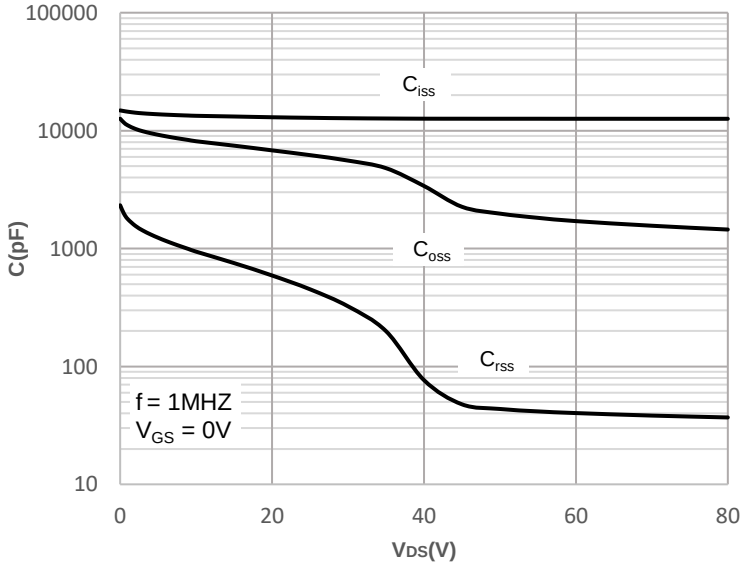


Figure 10: Capacitance Characteristics



Typical Performance Characteristics

Figure 11: Normalized Breakdown voltage vs. Junction Temperature

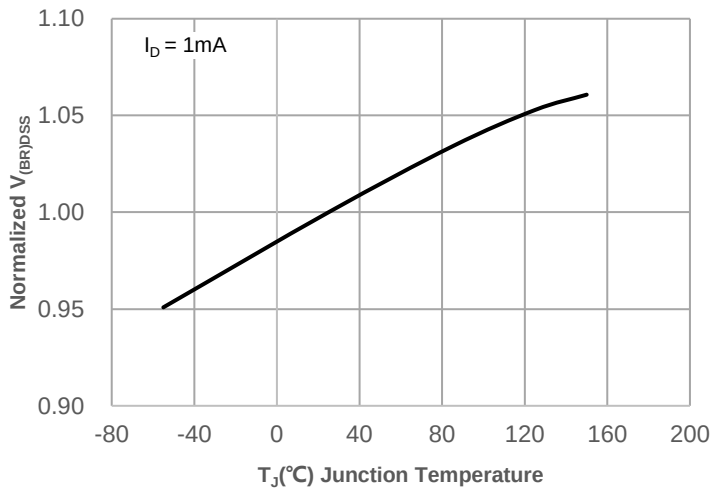


Figure 12: Normalized on Resistance vs. Junction Temperature

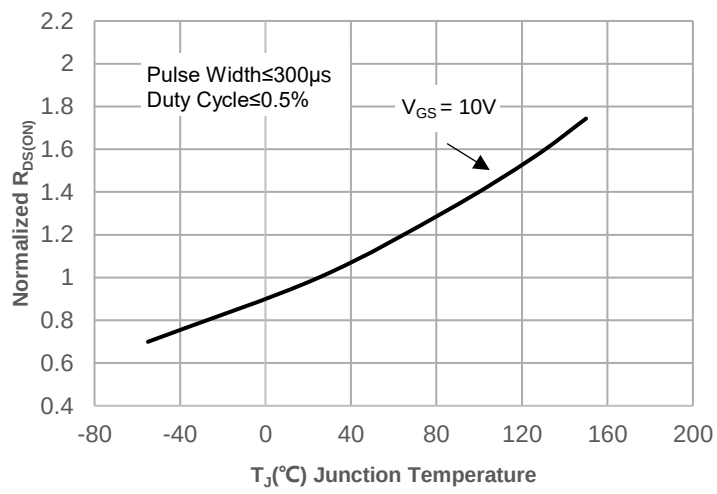


Figure 13: Normalized Threshold Voltage vs. Junction Temperature

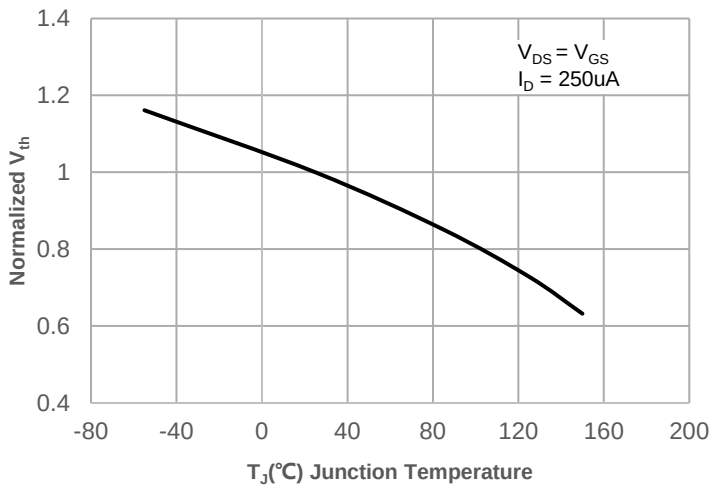


Figure 14: $R_{DS(ON)}$ vs. V_{GS}

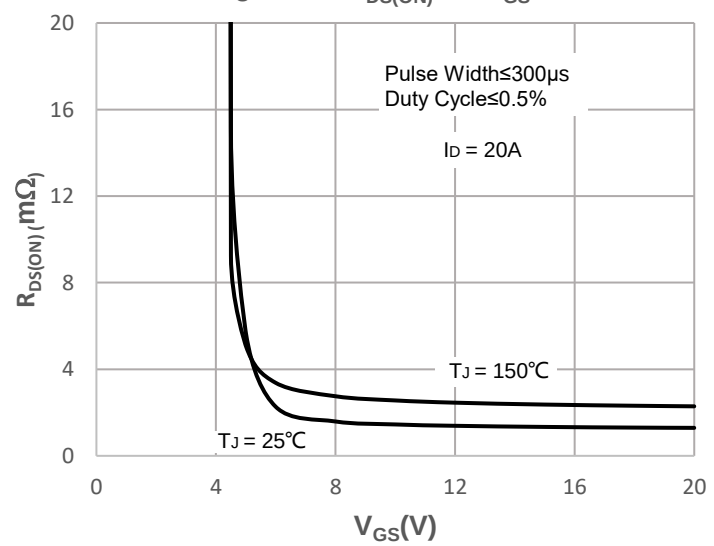
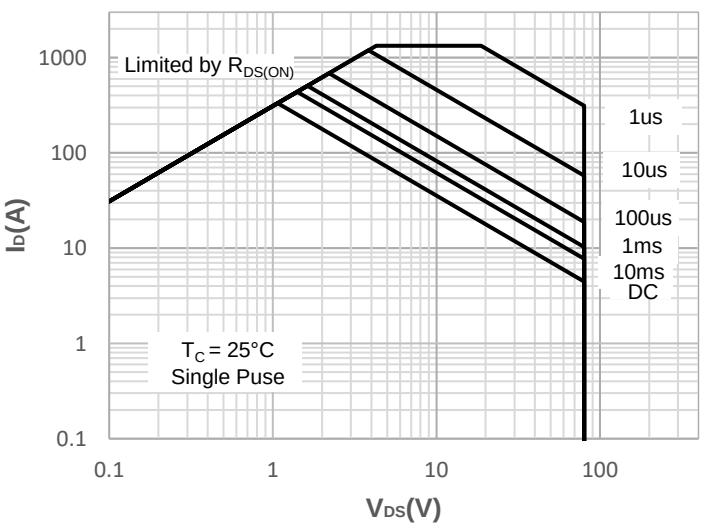


Figure 15: Maximum Safe Operating Area



Test Circuit

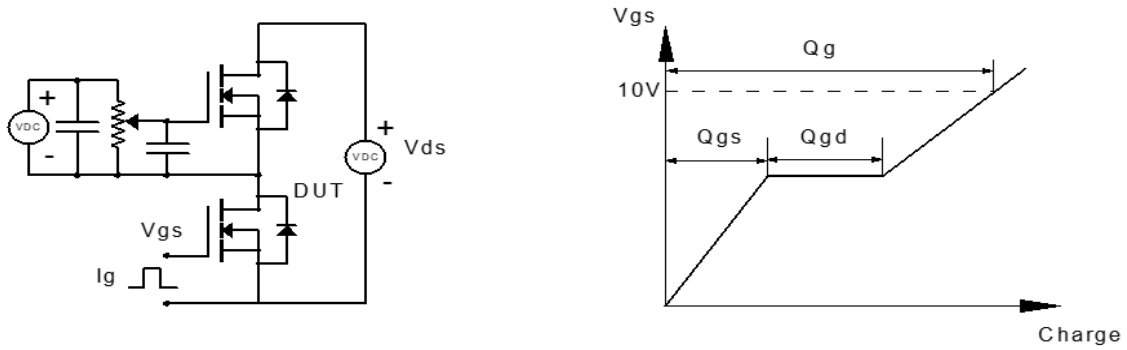


Figure 1: Gate Charge Test Circuit & Waveform

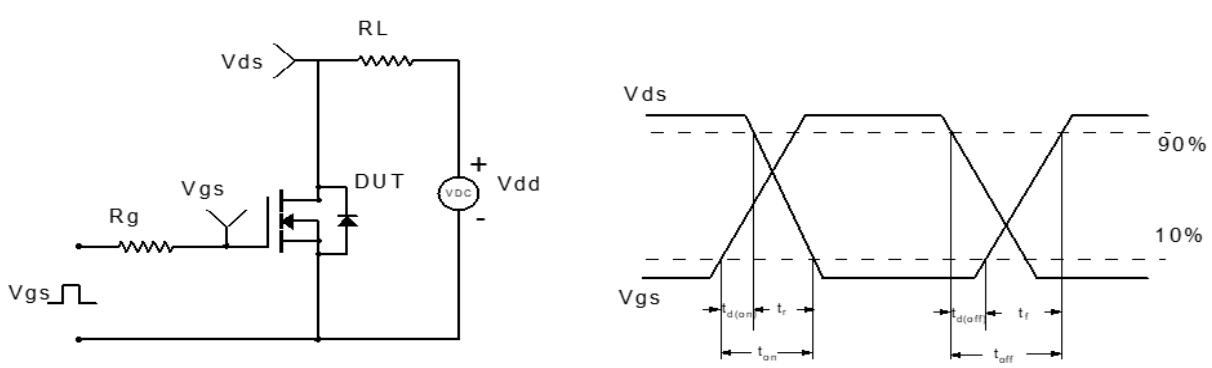


Figure 2: Resistive Switching Test Circuit & Waveform

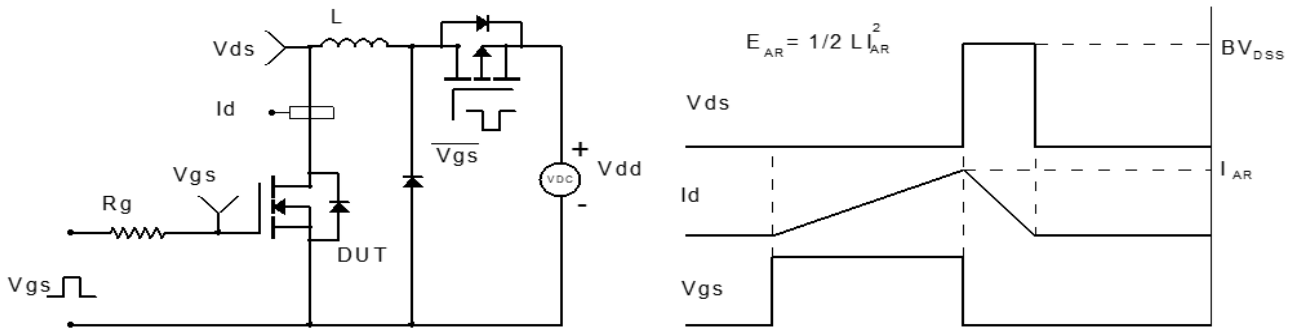


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

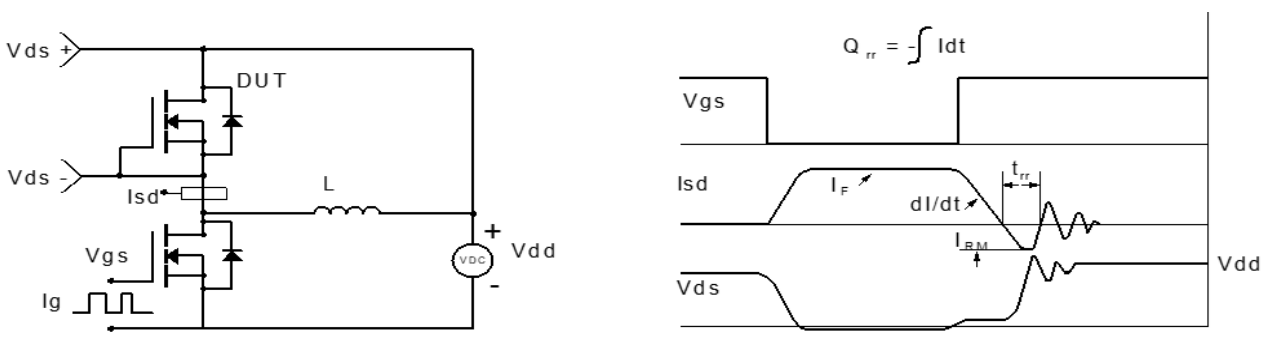
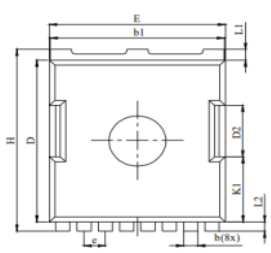


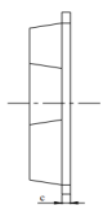
Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PowerJE®10x12)

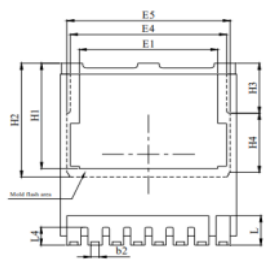
Package Outlines



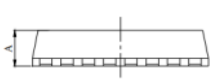
Top View



Side View



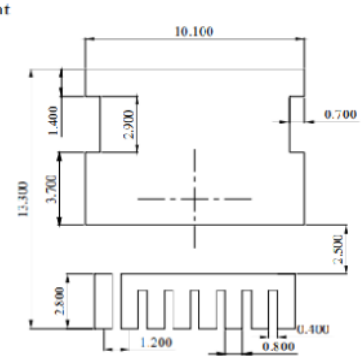
Bottom View



Front View

NOTES:
1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter.
3. Dimensions do not include burrs or mold flash. Mold flash or burrs does not exceed 0.150mm.

Recommended Soldering Footprint



DIMENSIONS:MILLIMETERS

DIM.	MILLIMETER		
	MIN	NOM	MAX
A	2.20	2.30	2.50
b	0.70	0.80	0.90
bl	9.70	9.80	9.90
b2	0.42	0.46	0.50
C	0.40	0.50	0.65
D	10.28	10.38	10.58
D2		3.30	
E	9.70	9.90	10.10
E1		7.80	
E4		8.80	
E5		9.20	
e		1.20(BSC)	
H	11.48	11.68	11.88
Hl	6.55	6.75	6.85
H2		7.30	
H3		3.20	
H4		3.80	
K1		4.18	
L	1.70	1.90	2.10
L1		0.70	
L2		0.60	
L4	1.00	1.15	1.30